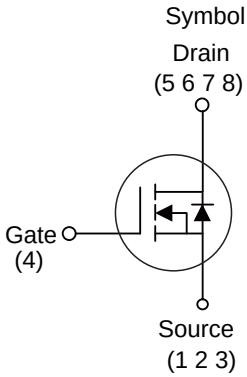
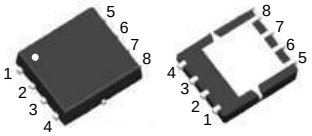
■ PRODUCT CHARACTERISTICS

V_{DSS}	60V
$R_{DS(ON)}$ Typ(@V_{GS}=10V)	13mΩ
$R_{DS(ON)}$ Typ(@V_{GS}=4.5V)	17mΩ
I_D	50A



■ APPLICATIONS

* Electronic lamp ballasts based on half bridge
* Load Switching,Quick/Wirelss Charge.
* Motor Driving



PDFN5X6

■ FEATURE

* Low Gate Charge
* Pb-Free Lead Plating

■ ORDER INFORMATION

Order Codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT6515G	PDFN5X6	5000 pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS(T_A=25°C,unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current Continuous(@V_{GS}=10V ,T_A=25°C)	I_D	50	A
Drain Current Continuous(@V_{GS}=10V ,T_A=100°C)	I_D	31	A
Drain Current Pulsed	I_{DM}	200	A
Avalanche Energy *	E_{AS}	110	mJ
Power Dissipation	P_D	75	W
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-55~ +150	°C

■ THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Unit
Junction to Case	R_{thJC}	1.66	°C/W

Note: * EAS condition: T_J=25°C ,V_{DS}=25V,V_G=10V ,L=0.5mH,R_g =25Ω

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off characteristics						
Drain to Source Breakdown Voltage	V_{DSS}	V_{GS}=0V,I_D=250μA	60	-	-	V
Drain to Source Leakage Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V	-	-	1	μA
Gate to Source Forward Leakage	$I_{GSS(F)}$	V_{GS}=+20V,V_{DS}=0V	-	-	100	nA
Gate to Source Reverse Leakage	$I_{GSS(R)}$	V_{GS}=-20V ,V_{DS}=0V	-	-	-100	nA
On characteristics						
Drain to Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V,I_D=20A	-	13	15	mΩ
		V_{GS}=4.5V,I_D=20A	-	17	20	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS},I_D=250μA	1	1.65	2.5	V
Dynamic characteristics						
Gate capacitance	R_g	V_{GS}=0V,V_{DS}=0V ,f=1.0MHz	-	1.4	-	Ω
Forward Transconductance	g_{fs}	V_{DS}=10V,I_D=3A	-	9.5	-	S
Input Capacitance	C_{iss}	V_{DS}=20V,V_{GS}=0V f=1.0MHz	-	2100	-	pF
Output Capacitance	C_{oss}		-	110	-	pF
Reverse Transfer Capacitance	C_{rss}		-	100	-	pF
Resistive Switching Characteristics						
Turn-on Delay Time	$t_{d(ON)}$	V_{GS}=10V, V_{DS}=30V, I_D=30A ,R_G=3Ω	-	9	-	ns
Rise Time	t_r		-	31	-	ns
Turn-off Delay Time	$t_{d(OFF)}$		-	44	-	ns
Fall Time	t_f		-	8	-	ns
Total Gate Charge	Q_g	I_D=30 A, V_{DS}=30V V_{GS}=10V	-	50	-	nC
Gate to Source Charge	Q_{gs}		-	10	-	nC
Gate to Drain("Miller") Charge	Q_{gd}		-	9	-	nC
Source-Drain Diode Characteristics						
Continuous Source Current(Body Diode)	I_S		-	-	50	A
Maximum Pulsed Current(Body Diode)	I_{SM}		-	-	200	A
Diode Forward Voltage	V_{SD}	I_{SD}=1A, V_{GS}=0V	-	0.71	1.2	V
Reverse Recovery Time	t_{rr}	I_{SD}=30A, T_J=25°C dI/dt=100A/μs	-	22	-	ns
Reverse Recovery Charge	Q_{rr}		-	25.5	-	nC

■ TYPICAL CHARACTERISTICS

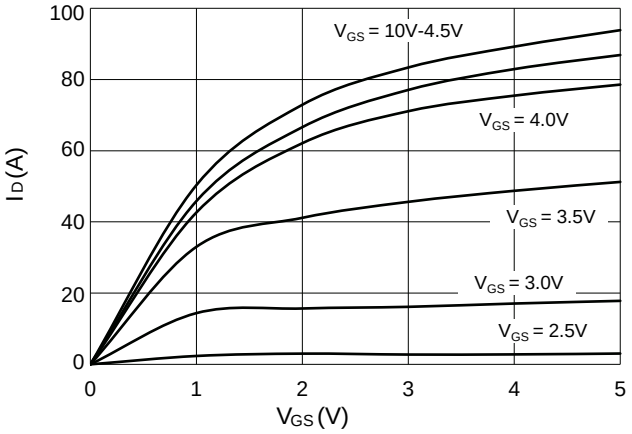


Figure 1: Output characteristics

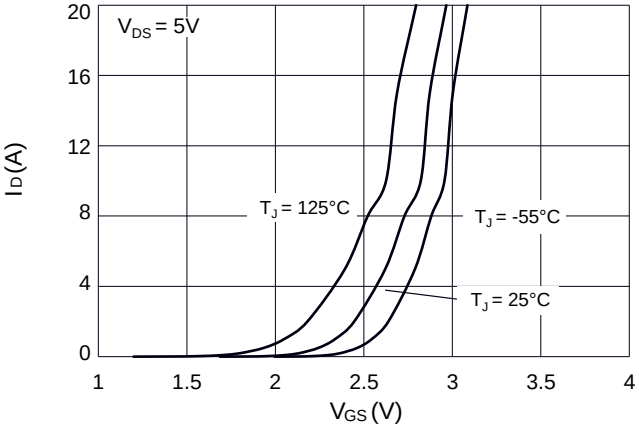


Figure 2: Transfer characteristics

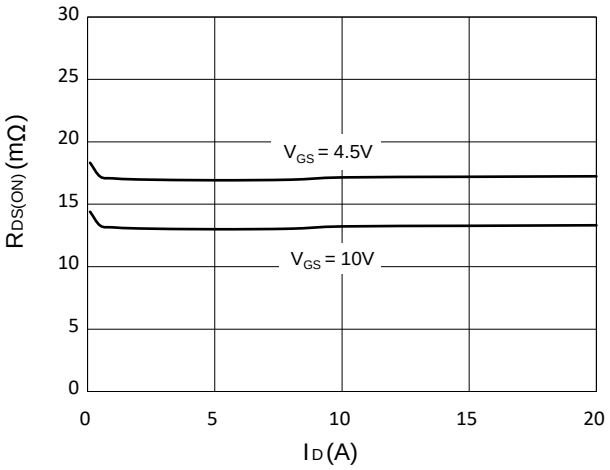


Figure 3: On-resistance vs.drain current

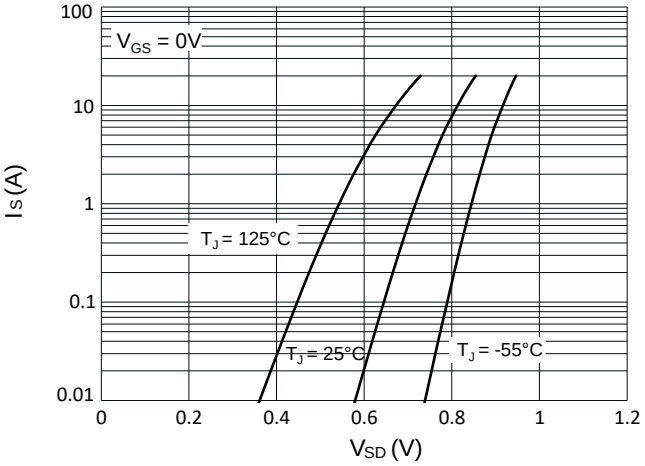


Figure 4: Body diode characteristics

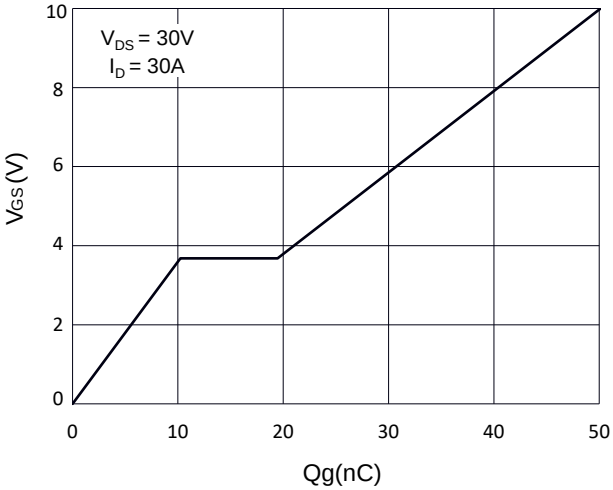


Figure 5: Gate charge characteristics

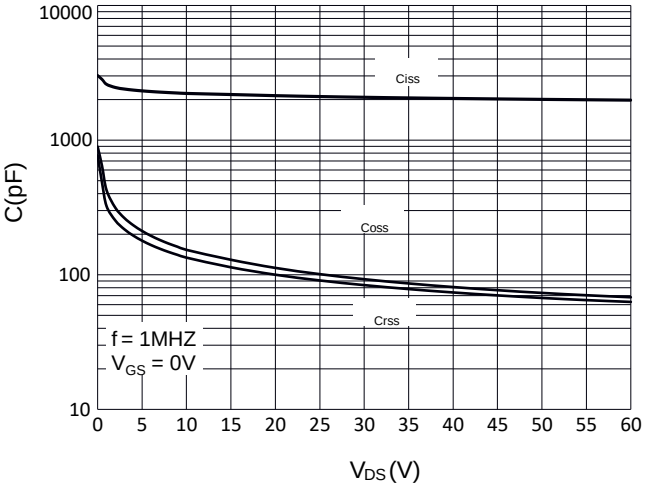


Figure 6: Capacitance characteristics

■ TYPICAL CHARACTERISTICS(Cont.)

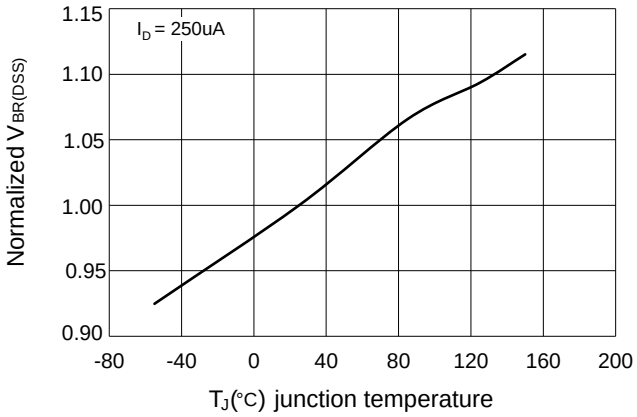


Figure 7: Normalized breakdown voltage vs. junction temperature

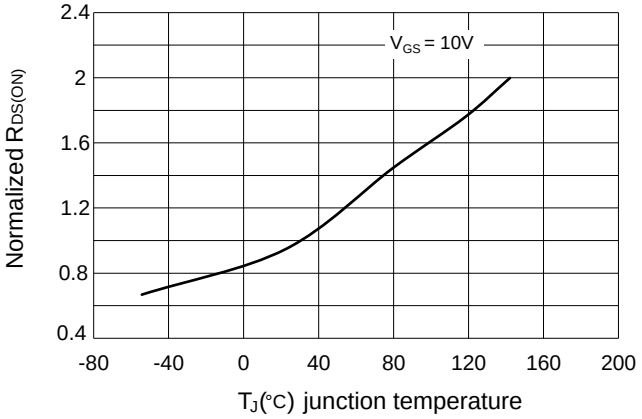


Figure 8: Normalized on-resistance vs. junction temperature

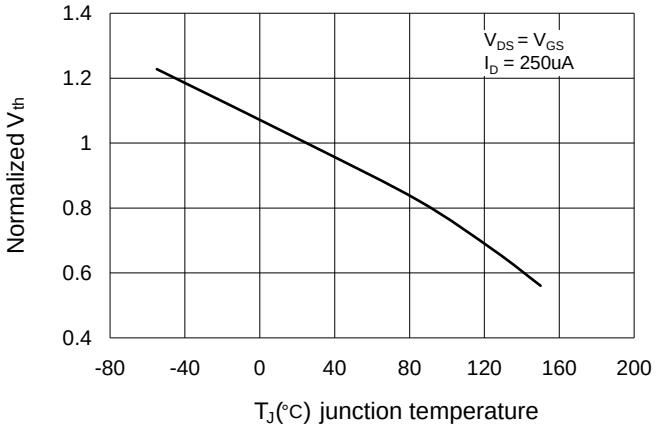


Figure 9: Normalized threshold voltage vs. junction temperature

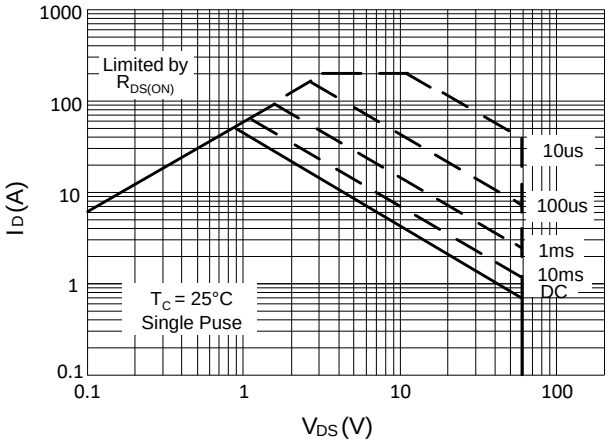
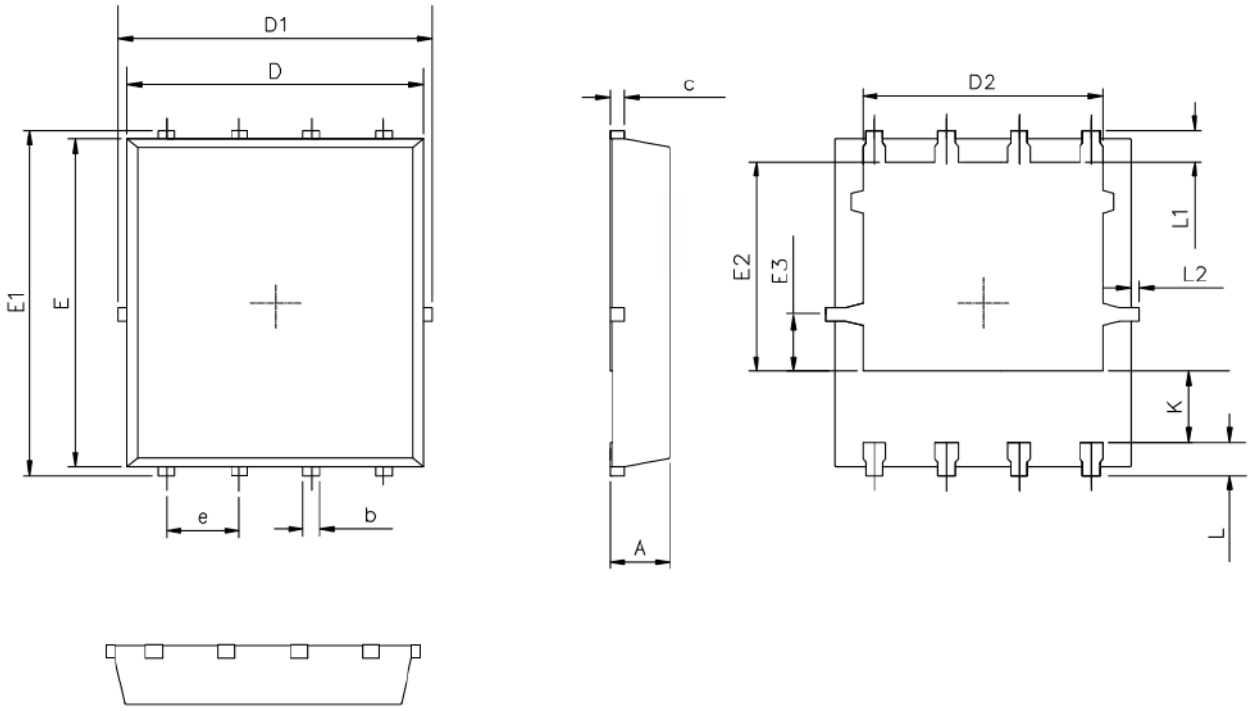


Figure 10: Maximum sffe operating area

■ PDFN5X6 PACKAGE OUTLINE DIMENSIONS



UNIT:mm

	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.25	0.35	0.50
c	0.10	0.20	0.30
D	4.80	5.00	5.30
D1	4.90	5.10	5.50
D2	3.92	4.02	4.20
E	5.65	5.75	5.85
E1	5.90	6.05	6.20
E2	3.325	3.525	3.775
E3	0.80	0.90	1.00
e		1.27	
L	0.40	0.55	0.70
L1		0.65	
L2	0.00		0.15
K	1.00	1.30	1.50

RECOMMENDED LAND PATTERN